

**A SEMICONDUCTOR DEVICE HAVING AN IMPLANTED  
PRECIPITATE REGION AND A METHOD OF MANUFACTURE THEREFOR**

**ABSTRACT OF THE DISCLOSURE**

The present invention provides a semiconductor device, a method of manufacture therefor and an integrated circuit including the same. The semiconductor device 100, among other things, may include a substrate 110 having a lattice structure and having an implanted precipitate region 120 located within the lattice structure. Additionally, the semiconductor device 100 may include a dynamic defect 125 located within the lattice structure and proximate the implanted precipitate region 120, such that the implanted precipitate region 120 affects a position of the dynamic defect 125 within the lattice structure. Located over the substrate 110 in the aforementioned semiconductor device 100 is a gate structure 160.